

**Effect of linear side-chain length on the photovoltaic
performance of benzodithiophene-*alt*-dicarboxylic ester
terthiophene polymers**

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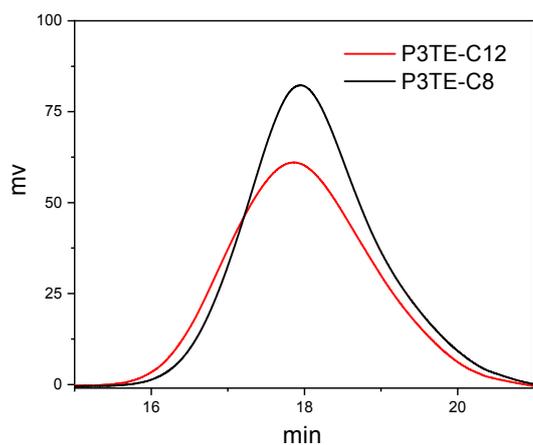


Figure S1. GPC curves for P3TE-C8 and P3TE-C12 measured at 145 °C.

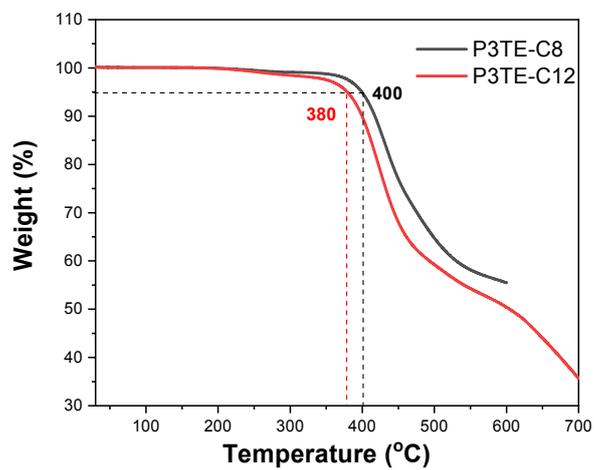


Figure S2. TGA curves for P3TE-C8 and P3TE-C12 measured under a nitrogen atmosphere at a heating rate of 10 °C/min.

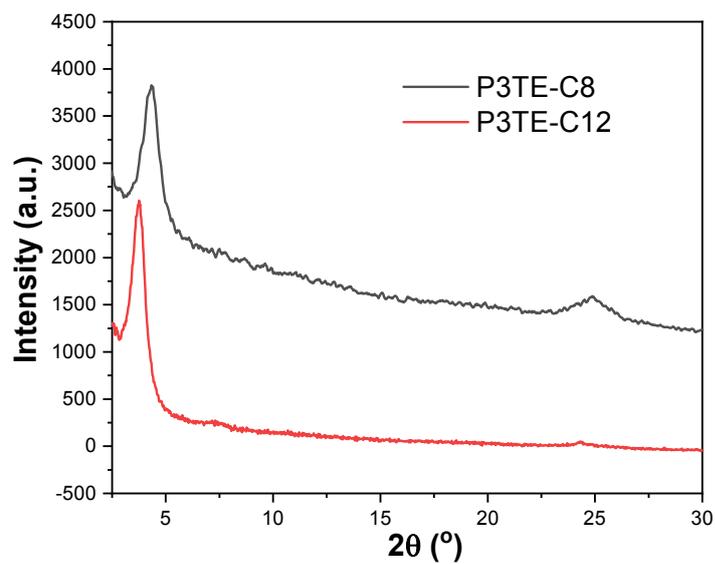


Figure S3. The XRD profiles of P3TE-C8 and P3TE-C12.

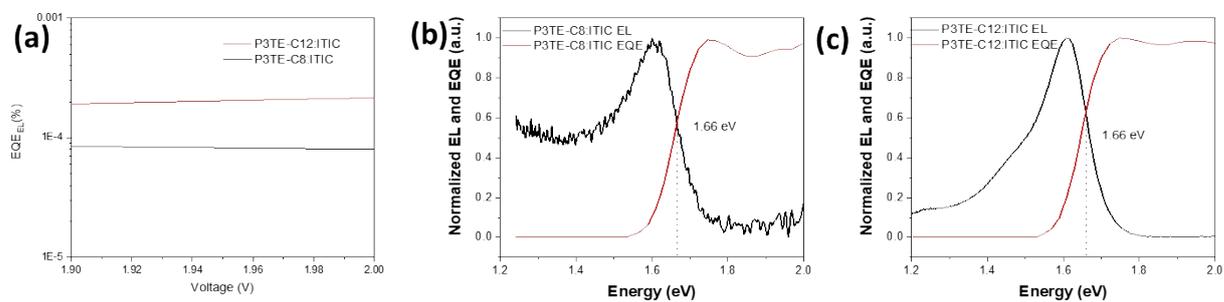


Figure S4. (a) The EQE_{EL} of P3TE-C8:ITIC and P3TE-C12:ITIC. The band gap of P3TE-C8:ITIC (b) and P3TE-C12:ITIC (c).

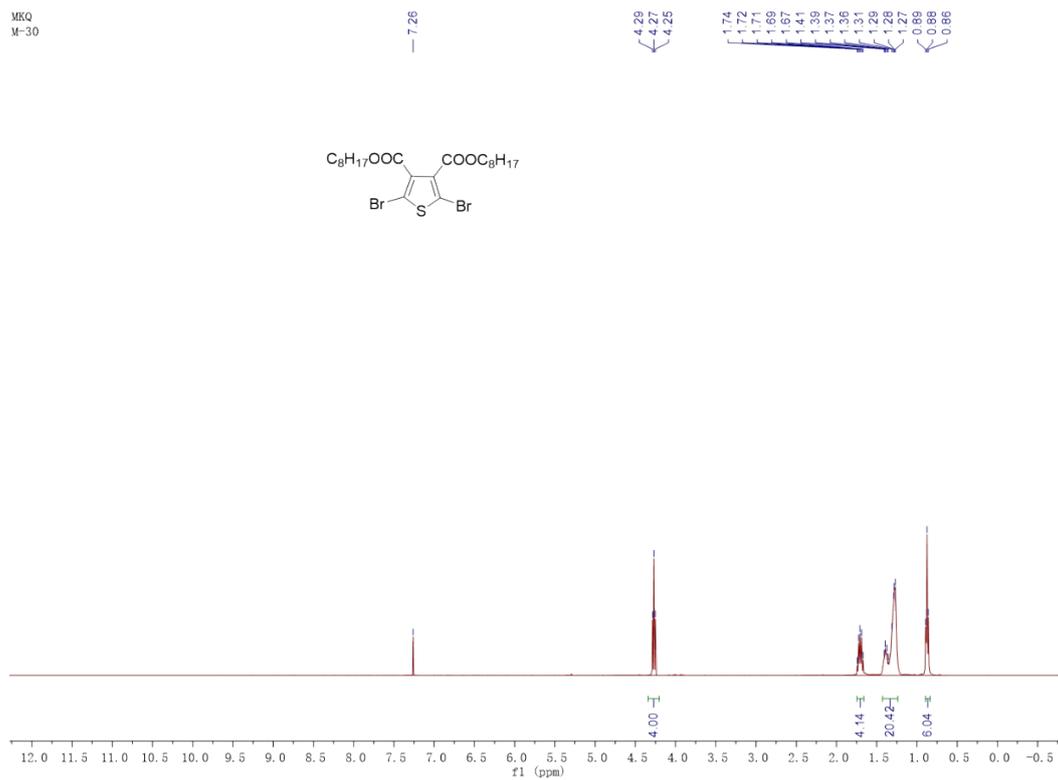


Figure S5. The ^1H -NMR spectra of compound **2a** in CDCl_3 .

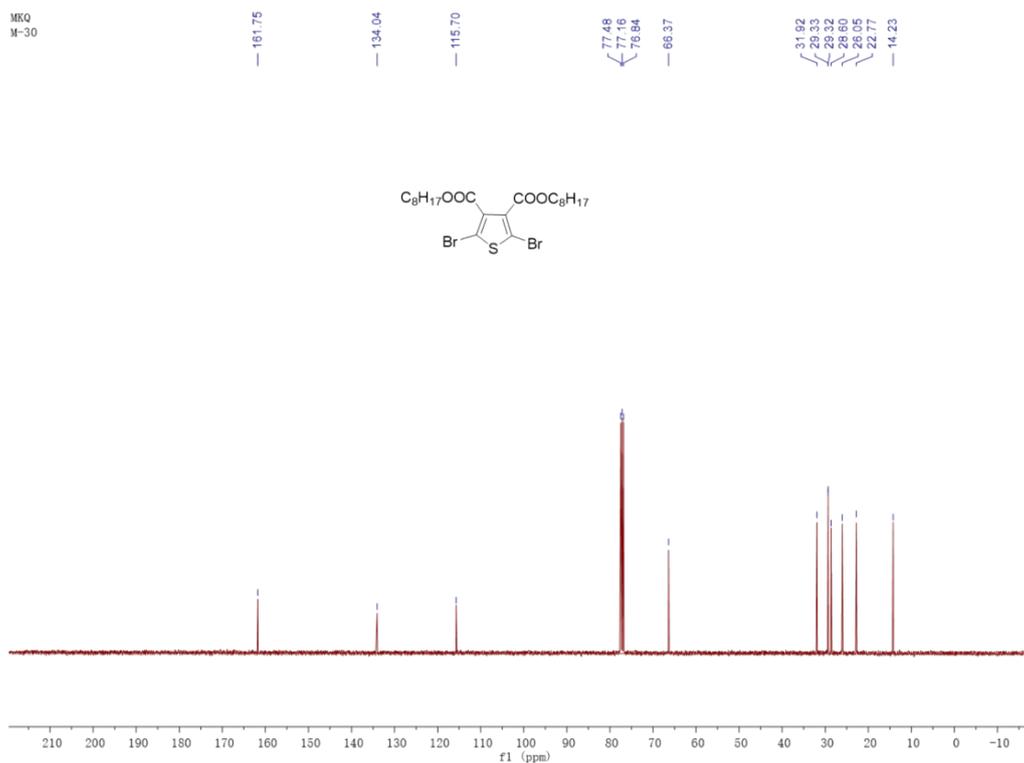


Figure S6. The ^{13}C -NMR spectra of compound **2a** in CDCl_3 .

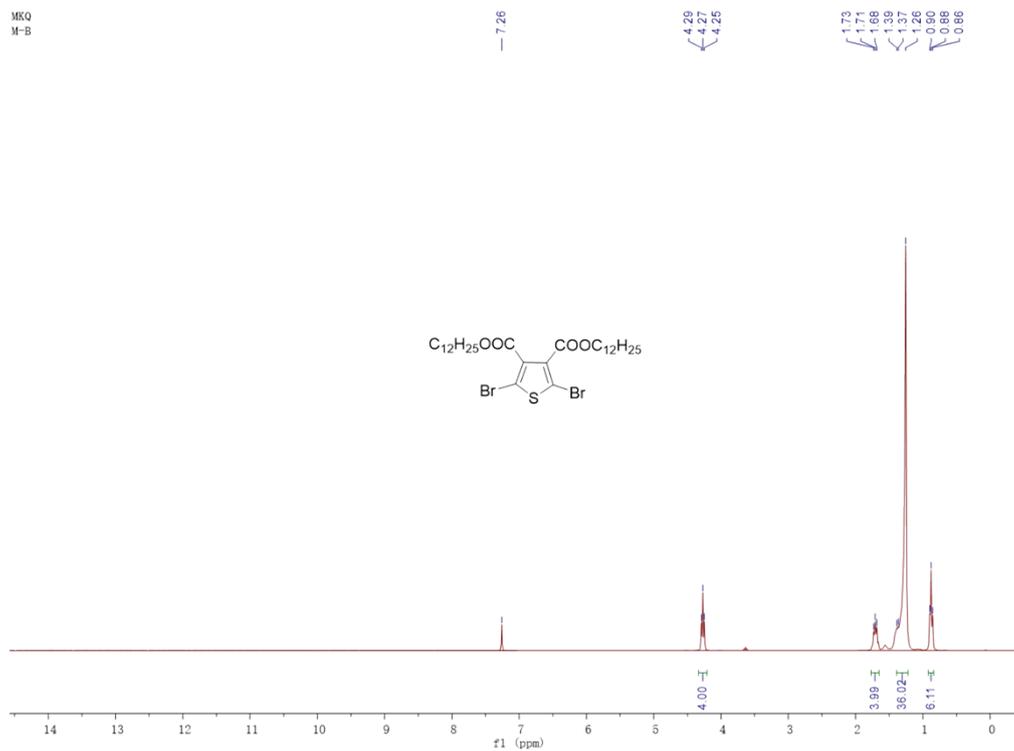


Figure S7. The ^1H -NMR spectra of compound **2b** in CDCl_3 .

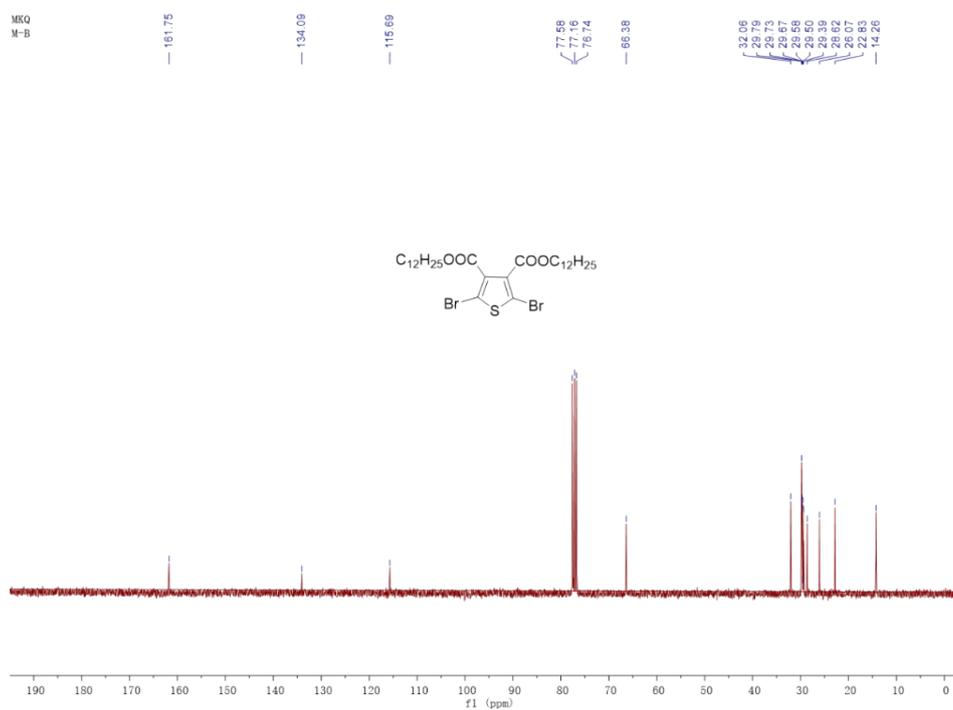


Figure S8. The ^{13}C -NMR spectra of compound **2b** in CDCl_3 .

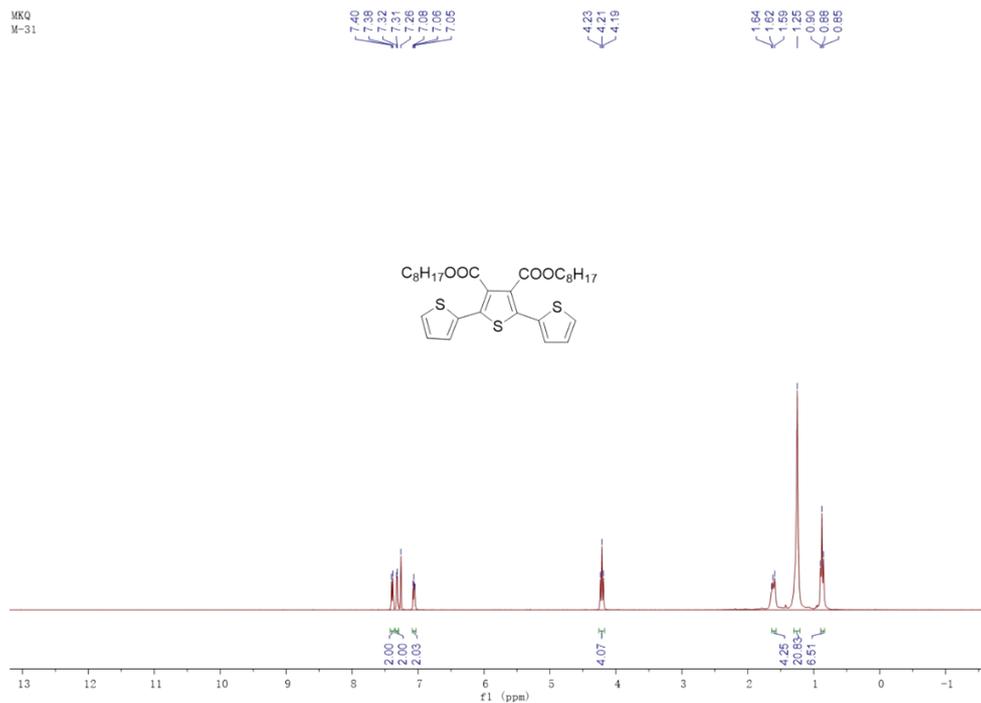


Figure S9. The 1H -NMR spectra of compound **3a** in $CDCl_3$.

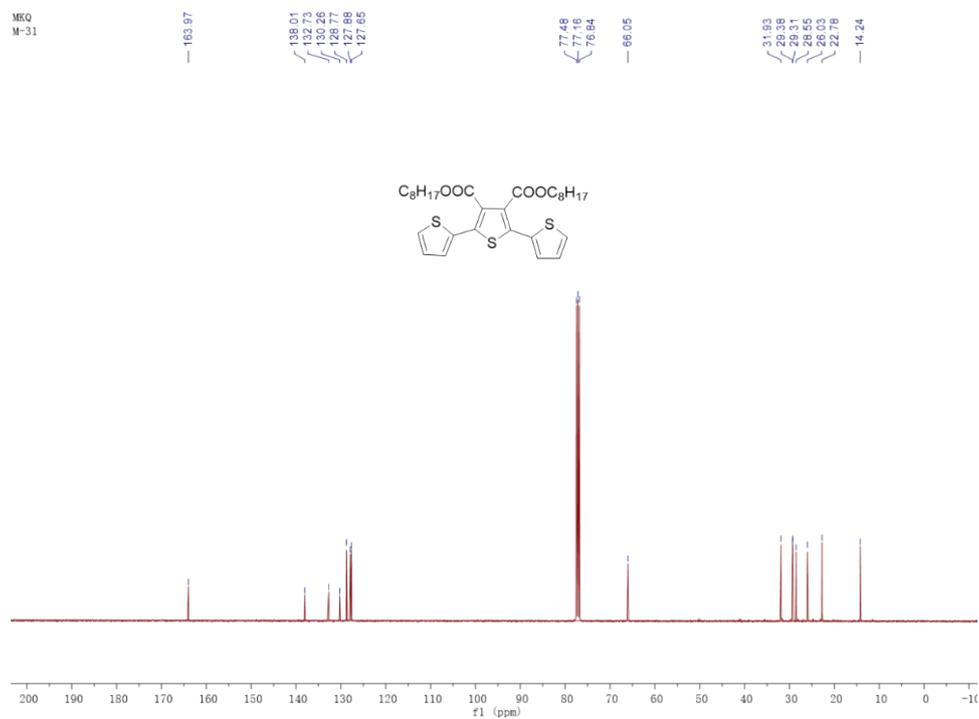


Figure S10. The ^{13}C -NMR spectra of compound **3a** in $CDCl_3$.

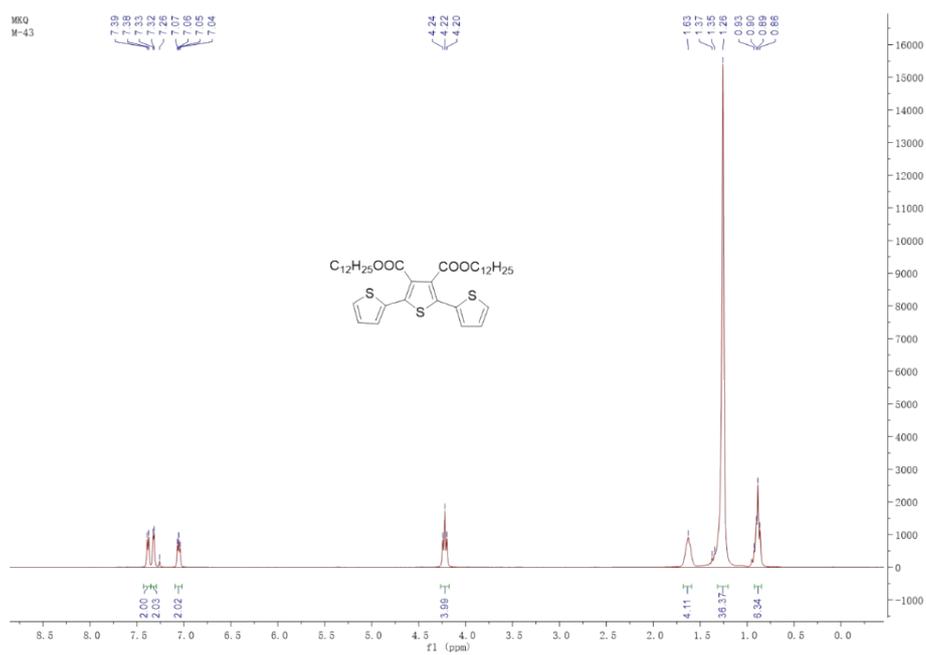


Figure S11. The ^1H -NMR spectra of compound **3b** in CDCl_3 .

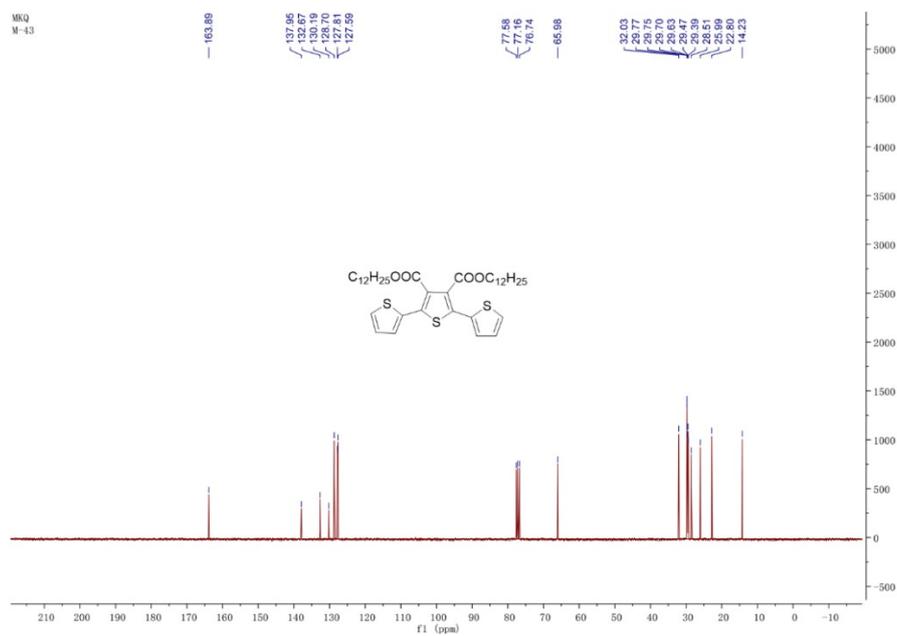


Figure S12. The ^{13}C -NMR spectra of compound **3b** in CDCl_3 .

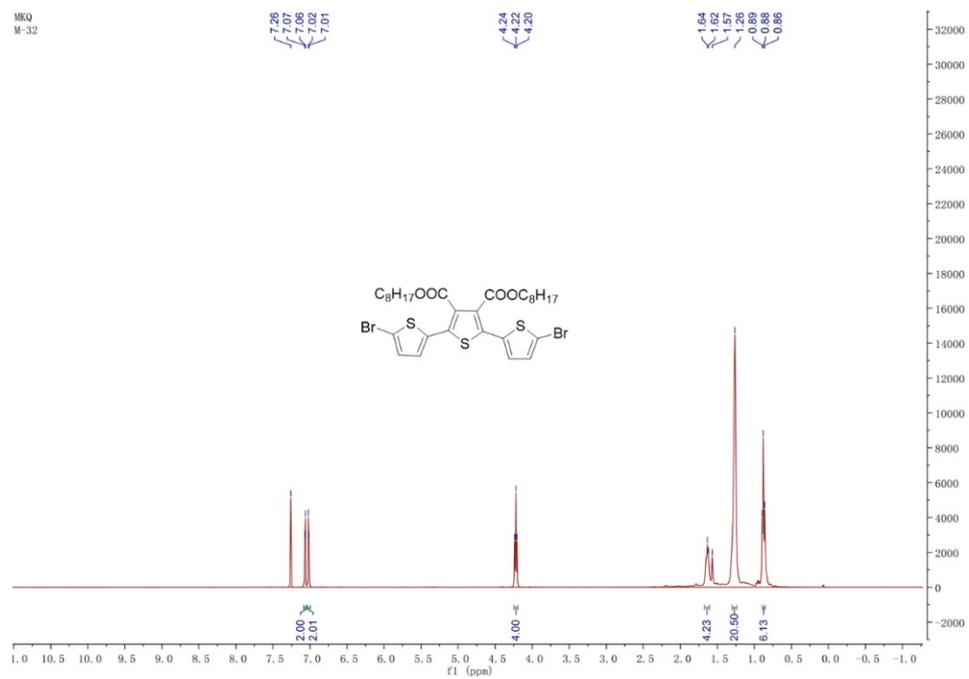


Figure S13. The $^1\text{H-NMR}$ spectra of compound **4a** in CDCl_3 .

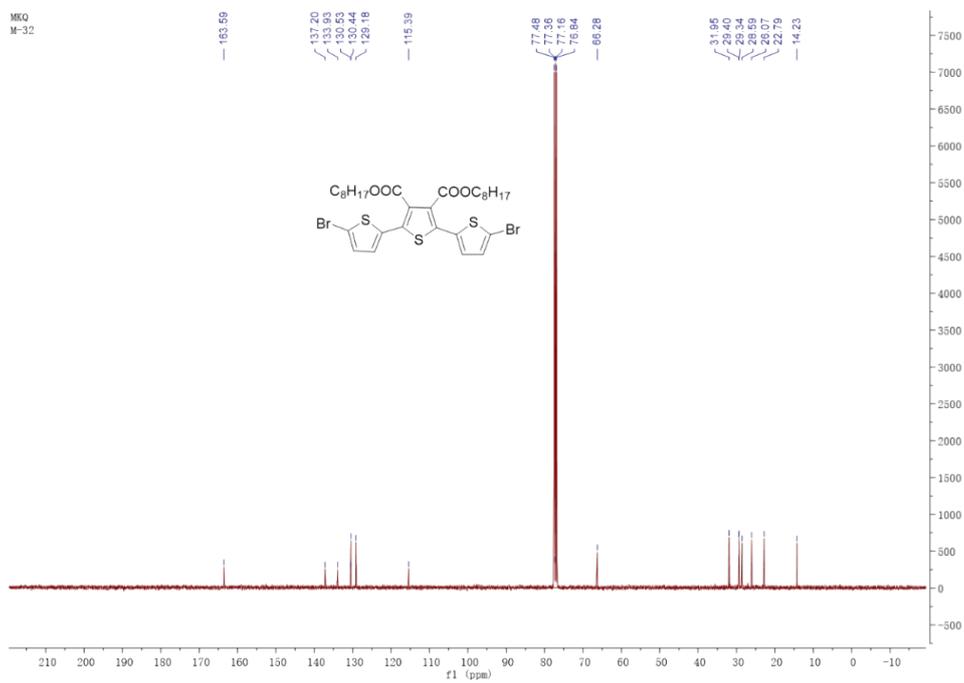


Figure S14. The $^{13}\text{C-NMR}$ spectra of compound **4a** in CDCl_3 .

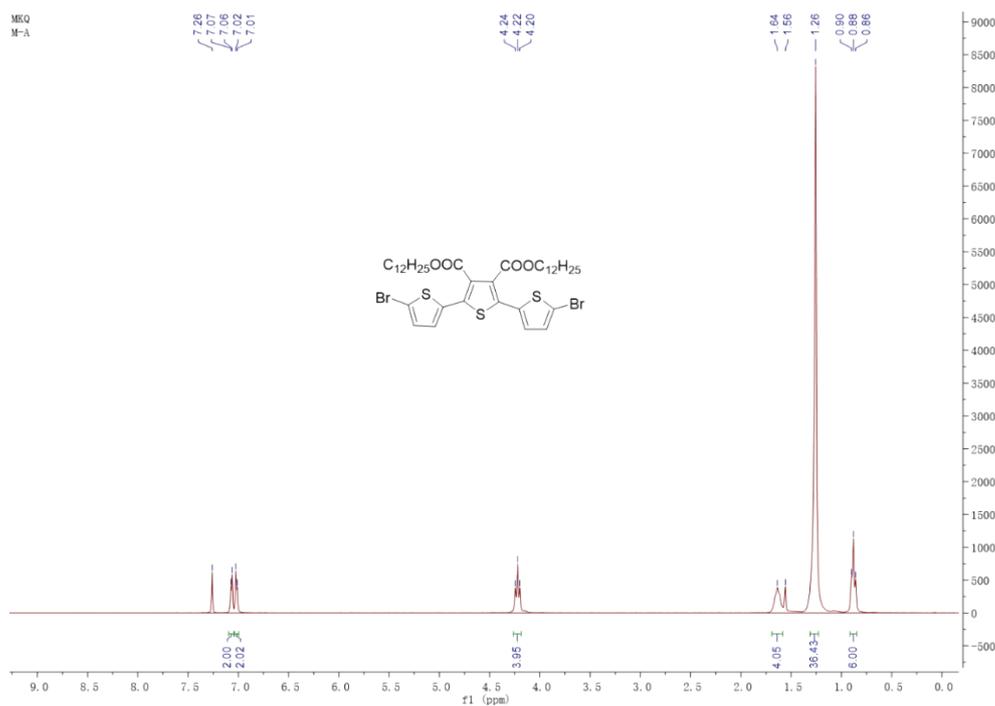


Figure S15. The ¹H-NMR spectra of compound **4b** in CDCl₃.

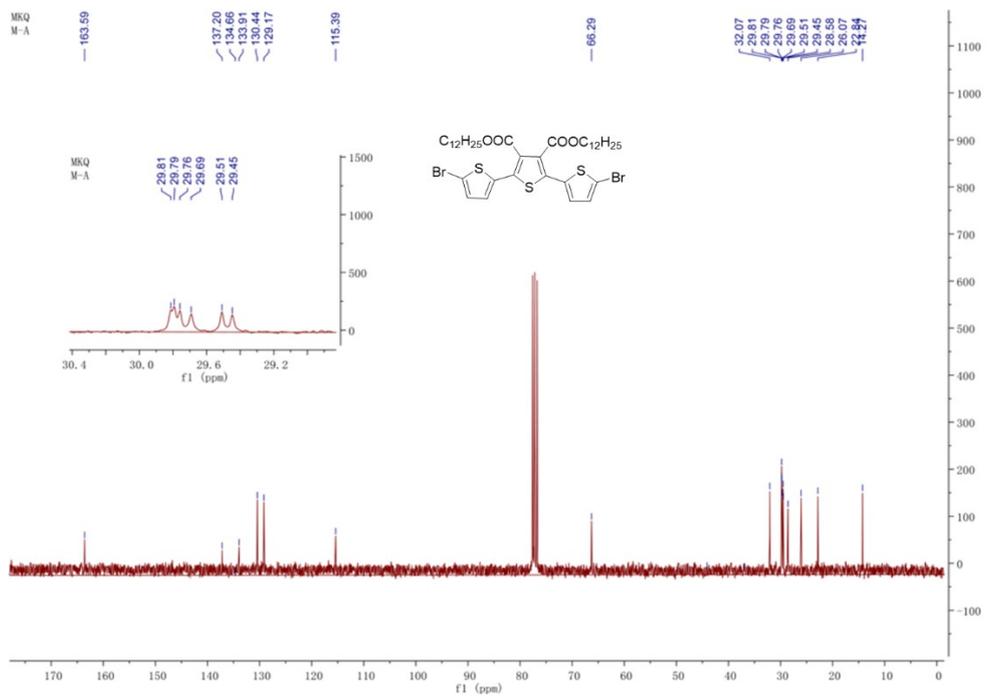


Figure S16. The ¹³C-NMR spectra of compound **4b** in CDCl₃.

Table S1. The best photovoltaic parameters of P3TE-C8:ITIC with different D:A weight ratios (w/w).

D:A ratio	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
1.5:1	0.797	12.70	45.29	4.58
1:1	0.777	13.52	42.38	4.45
1:1.5	0.769	13.52	40.66	4.23

P3TE-C8:ITIC was dissolved in chlorobenzene solution with a concentration of 10 mg mL⁻¹. The solution was heated to 40 °C until total dissolution. The resulting solution was spin-coated onto PEDOT:PSS modified ITO in succession. The thickness (around 90 nm) of film was controlled the spin-coating speed at 1500-2000 r.m.p. Subsequently, the active layer was annealed at 100 °C for 10 min.

Table S2. The best photovoltaic parameters of P3TE-C8:ITIC with different DIO ratios.

DIO ratio	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
0	0.797	12.70	45.29	4.58
0.5%	0.814	12.80	52.48	5.47
1%	0.809	12.24	44.57	4.42
2%	0.815	9.96	39.44	3.20

P3TE-C8:ITIC (1.5:1 w/w) were dissolved in chlorobenzene solution with a concentration of 10 mg mL⁻¹. The solution was heated to 40 °C until total dissolution. The DIO was added into above solution. After 30 min, the resulting solution was spin-coated onto PEDOT:PSS modified ITO in succession. The thickness (around 90 nm) of film was controlled the spin-coating speed at 1500 r.m.p. Subsequently, the active layer was annealed at 100 °C for 10 min.

Table S3. The best photovoltaic parameters of P3TE-C8:ITIC with different annealing temperatures.

Annealing temperature (°C)	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
80	0.827	12.13	49.25	4.94
100	0.814	12.86	52.48	5.47
120	0.825	12.71	50.61	5.31
140	0.828	11.59	52.21	5.30
160	0.829	11.40	51.78	4.89

P3TE-C8:ITIC (1.5:1 w/w) were dissolved in chlorobenzene solution with a concentration of 10 mg mL⁻¹. The solution was heated to 40 °C until total dissolution. The 0.5% DIO was added into above solution. After 30 min, the resulting solution was spin-coated onto PEDOT:PSS modified ITO in succession. The thickness (around 90 nm) of film was controlled the spin-coating speed at 1500 r.m.p. Subsequently, the active layer was annealed at 80-160 °C for 10 min.

Table S4. The best photovoltaic parameters of P3TE-C12:ITIC with different D:A weight ratios (w/w).

D:A ratio	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
1.5:1	0.917	10.15	57.54	5.36
1:1	0.916	12.83	52.06	6.12
1:1.5	0.907	12.46	49.48	5.59

P3TE-C12:ITIC was dissolved in chlorobenzene solution with a concentration of 10 mg mL⁻¹. The solution was heated to 40 °C until total dissolution. The resulting solution was spin-coated onto PEDOT:PSS modified ITO in succession. The thickness (around 90 nm) of film was controlled the spin-coating speed at 1500-2000 r.m.p. Subsequently, the active layer was annealed at 100 °C for 10 min.

Table S5. The best photovoltaic parameters of P3TE-C12:ITIC with different DIO ratios.

DIO ratio	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
0	0.916	12.83	52.06	6.12
0.5%	0.904	13.81	55.96	6.99
1%	0.885	11.56	42.86	4.39
2%	0.888	10.14	37.26	3.35

P3TE-C12:ITIC (1:1 w/w) were dissolved in chlorobenzene solution with a concentration of 10 mg mL⁻¹. The solution was heated to 40 °C until total dissolution. The DIO was added into above solution. After 30 min, the resulting solution was spin-coated onto PEDOT:PSS modified ITO in succession. The thickness (around 90 nm) of film was controlled the spin-coating speed at 1700 r.m.p. Subsequently, the active layer was annealed at 100 °C for 10 min.

Table S6. The best photovoltaic parameters of P3TE-C12:ITIC with different annealing temperatures.

Annealing temperature (°C)	V_{OC} (V)	J_{SC} (mA cm ⁻²)	FF (%)	PCE (%)
80	0.903	14.25	53.99	6.95
100	0.904	13.81	55.96	6.99
120	0.909	13.50	58.09	7.13
140	0.906	14.20	59.36	7.64
160	0.890	12.57	60.25	6.74

P3TE-C12:ITIC (1:1 w/w) were dissolved in chlorobenzene solution with a concentration of 10 mg mL⁻¹. The solution was heated to 40 °C until total dissolution. The 0.5% DIO was added into above solution. After 30 min, the resulting solution was spin-coated onto PEDOT:PSS modified ITO in succession. The thickness (around 90 nm) of film was controlled the spin-coating speed at 1700 r.m.p. Subsequently, the active layer was annealed at 80-160 °C for 10 min.

Table S7. The detailed energy losses of P3TE-C8:ITIC and P3TE-C12:ITIC-based devices.

	E_{gap} (eV)	qV_{oc} (eV)	$q\Delta V$ (eV)	ΔE_1 (eV)	ΔE_2 (eV)	EQE_{EL}	ΔE_3 (eV)
P3TE-C8:ITIC	1.66	0.814	0.846	0.276	0.207	7.97E-7	0.363
P3TE-C12:ITIC	1.66	0.906	0.754	0.276	0.141	2.18E-6	0.337